Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in an MLPAK33 (SOT8002) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- Ultra low Q_G and Q_{GD} for high system efficiency, especially at higher switching frequencies
- · Superfast switching with soft-recovery
- · Low spiking and ringing for low EMI designs
- MLPAK33 package (3.3 x 3.3 mm footprint)

3. Applications

- DC to DC conversion
- · Battery management
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	18.3	А
Static characte	ristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 11.4 A; T _j = 25 °C		-	7.1	8.3	mΩ
		V_{GS} = 4.5 V; I_{D} = 9.8 A; T_{j} = 25 °C		-	8.9	11.1	mΩ
Dynamic chara	cteristics						
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I_{D} = 9.8 A; V_{GS} = 4.5 V; T_{j} = 25 °C		-	5.1	7.7	nC

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	D
2	S	source		
3	S	source		G—(FA)
4	G	gate	l h d	mbb076 S
5	D	drain		
6	D	drain		
7	D	drain	MLPAK33 (SOT8002-1)	
8	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PXN8R3-30QL		plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-1				

7. Marking

Table 4. Marking codes

Type number	Marking code
PXN8R3-30QL	9AD

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	18.3	Α
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	11.4	Α
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	7.2	Α
		V _{GS} = 10 V; T _{sp} = 25 °C		-	31	Α
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	293	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; t ≤ 5 s	[1]	-	4.3	W
			[1]	-	1.7	W
		T _{sp} = 25 °C		-	12.5	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode		•	'		
Is	source current	T _{amb} = 25 °C	[1]	-	1.5	Α
Avalanche rug	ggedness		'	'		,
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	T _{j(init)} = 25 °C; I _D = 1.7 A; DUT in avalanche (unclamped)		-	25	mJ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

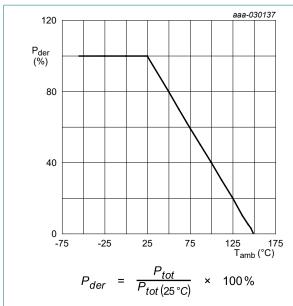


Fig. 1. Normalized total power dissipation as a function of ambient temperature

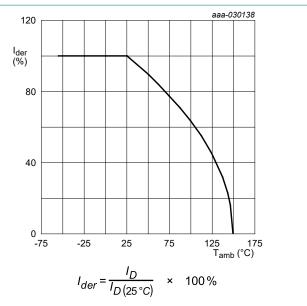


Fig. 2. Normalized continous drain current as a function of ambient temperature

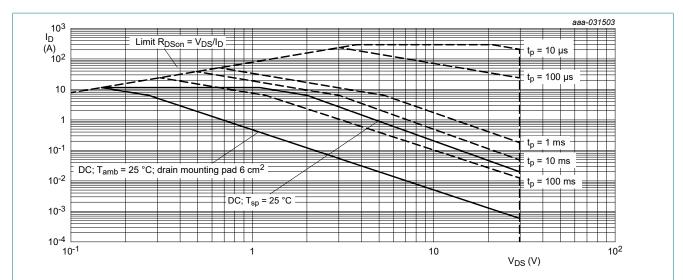


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-a)	thermal resistance from	in free air [[1]	-	150	190	K/W
	junction to ambient		[2]	-	60	75	K/W
		in free air; t ≤ 5 s	[2]	-	24	29	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	7	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

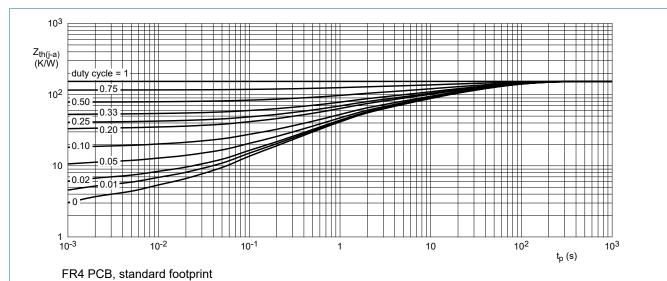


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

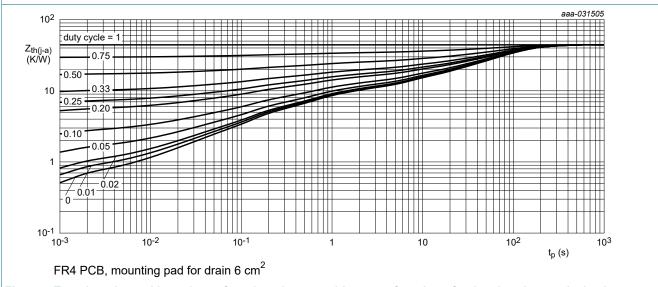


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V, N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		l e			
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.2	1.7	2.2	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.1	μΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-0.1	μΑ
R _{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 11.4 \text{ A}; T_j = 25 \text{ °C}$	-	7.1	8.3	mΩ
03011	resistance	V _{GS} = 10 V; I _D = 11.4 A; T _j = 150 °C	-	11	12.9	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 9.8 \text{ A}; T_j = 25 \text{ °C}$	-	8.9	11.1	mΩ
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 11.4 \text{ A}; T_j = 25 \text{ °C}$	-	25	-	S
R _G	gate resistance	f = 1 MHz	-	2.3	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I_{D} = 11.4 A; V_{GS} = 10 V; I_{j} = 25 °C	-	10.6	15.9	nC
		$V_{DS} = 15 \text{ V}; I_D = 9.8 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	5.1	7.7	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.9	-	nC
Q _{GS(th)}	pre-threshold gate- source charge		-	1.2	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	0.7	-	nC
Q _{GD}	gate-drain charge		-	1.3	-	nC
V_{GSpl}	gate-source plateau voltage	V _{DS} = 15 V; I _D = 9.8 A; T _j = 25 °C	-	2.6	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	760	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	270	-	pF
C _{rss}	reverse transfer capacitance		-	42	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 9.8 A; V _{GS} = 4.5 V;	-	5	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	8	-	ns
$t_{d(off)}$	turn-off delay time		-	6	-	ns
t _f	fall time		-	3	-	ns
Source-dra	in diode		'			
V _{SD}	source-drain voltage	I _S = 1.5 A; V _{GS} = 0 V; T _j = 25 °C	-	0.7	1.2	V
t _{rr}	reverse recovery time	I _S = 1.5 A; dI _S /dt = -100 A/μs;	-	15	-	ns
Q _r	recovered charge	$V_{GS} = 4.5 \text{ V}; V_{DS} = 15 \text{ V}; T_j = 25 \text{ °C}$	-	6	-	nC
t _a	reverse recovery rise time		-	8	-	ns
t _b	reverse recovery fall time	1	-	7	-	ns

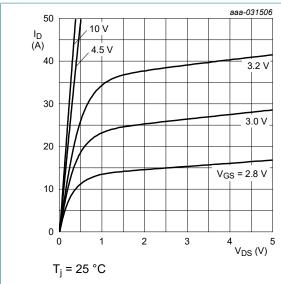


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

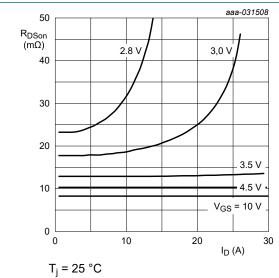


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

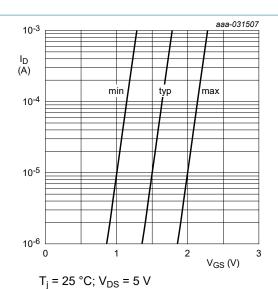


Fig. 7. Subthreshold drain current as a function of gate-source voltage

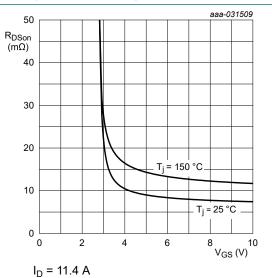


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

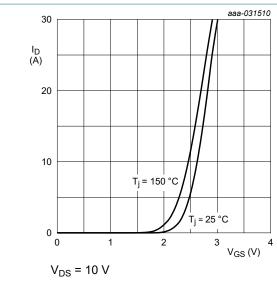


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

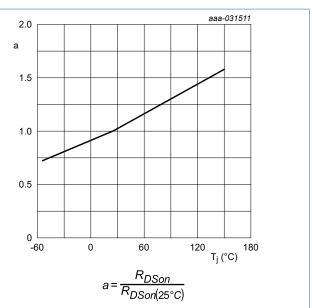


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

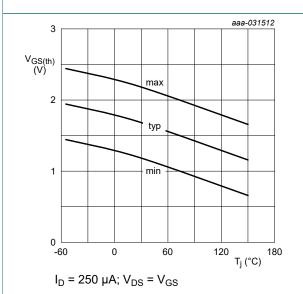


Fig. 12. Gate-source threshold voltage as a function of junction temperature

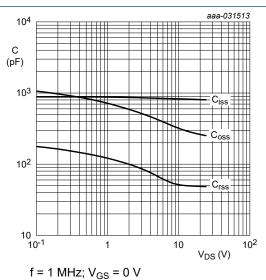


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

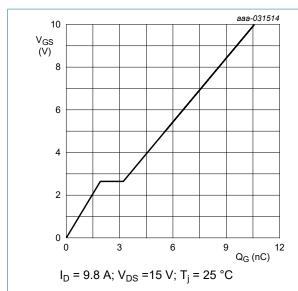


Fig. 14. Gate-source voltage as a function of gate charge; typical values

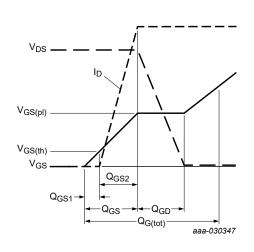


Fig. 15. Gate charge waveform definitions

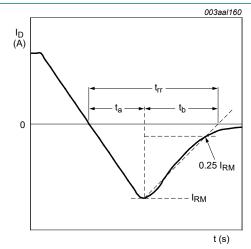


Fig. 16. Reverse recovery timing definition

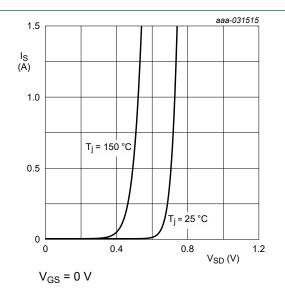
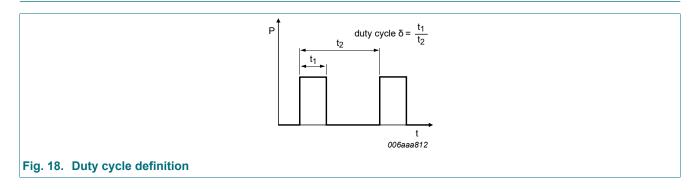


Fig. 17. Source current as a function of source-drain voltage; typical values

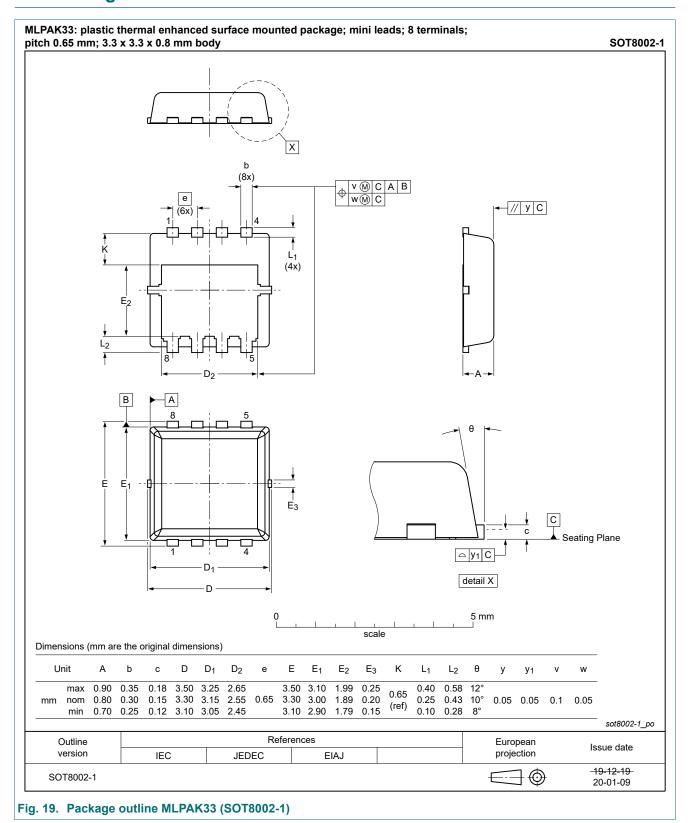
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11. Test information



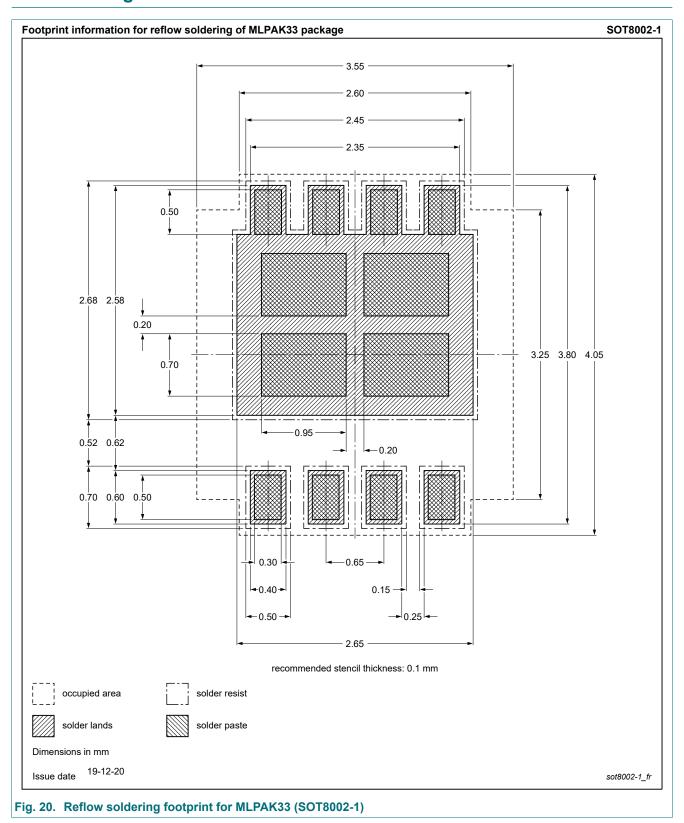
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

The second secon							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PXN8R3-30QL v.2	20201102	Product data sheet	-	PXN8R3-30QL v.1			
Modifications:	Chapter "Thermal characteristics": Typo corrected.						
PXN8R3-30QL v.1	20200428	Preliminary data sheet	-	-			

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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